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What is "[Embedded - Microcontrollers](#)"?

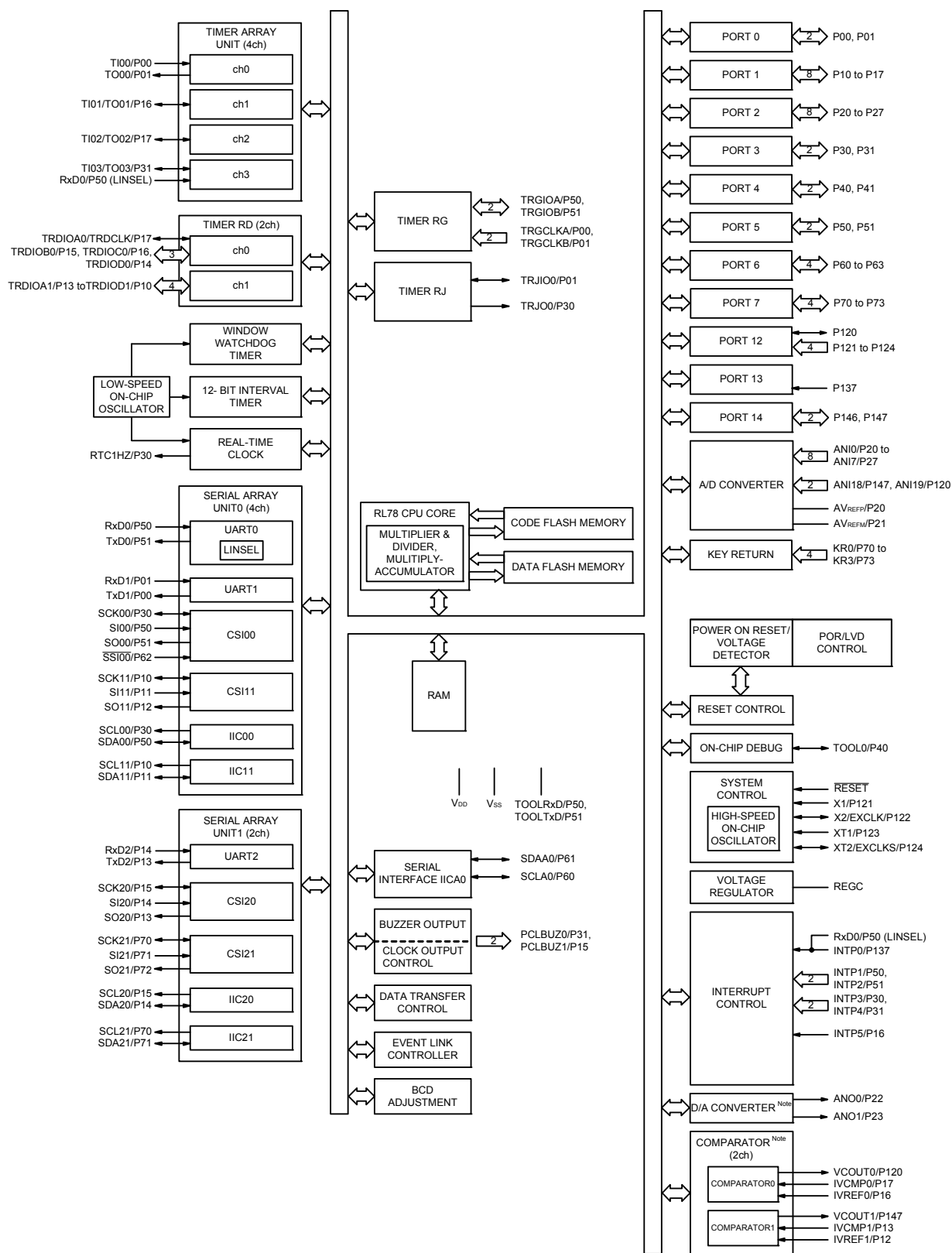
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

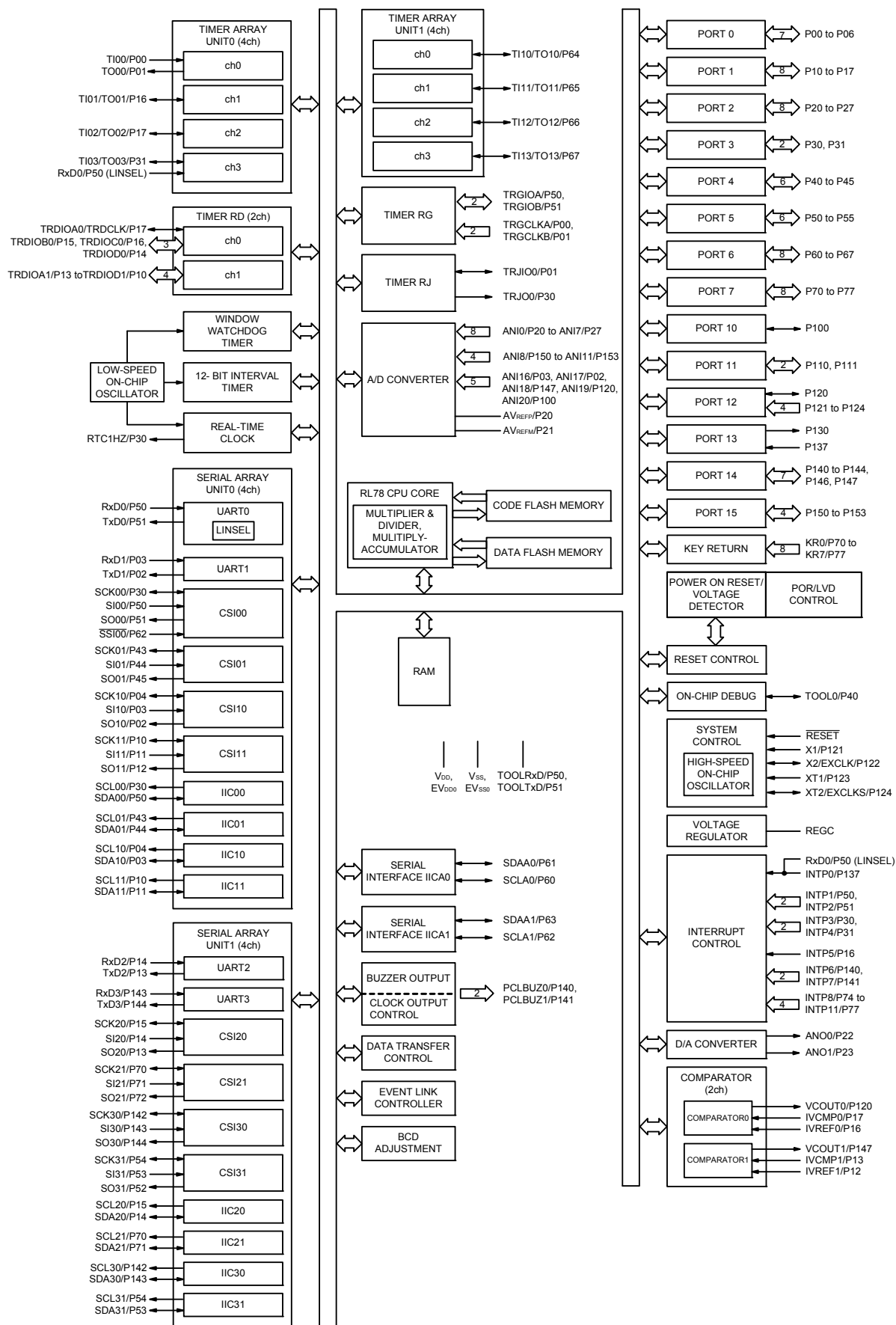
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104lgafb-30

1.5.5 44-pin products

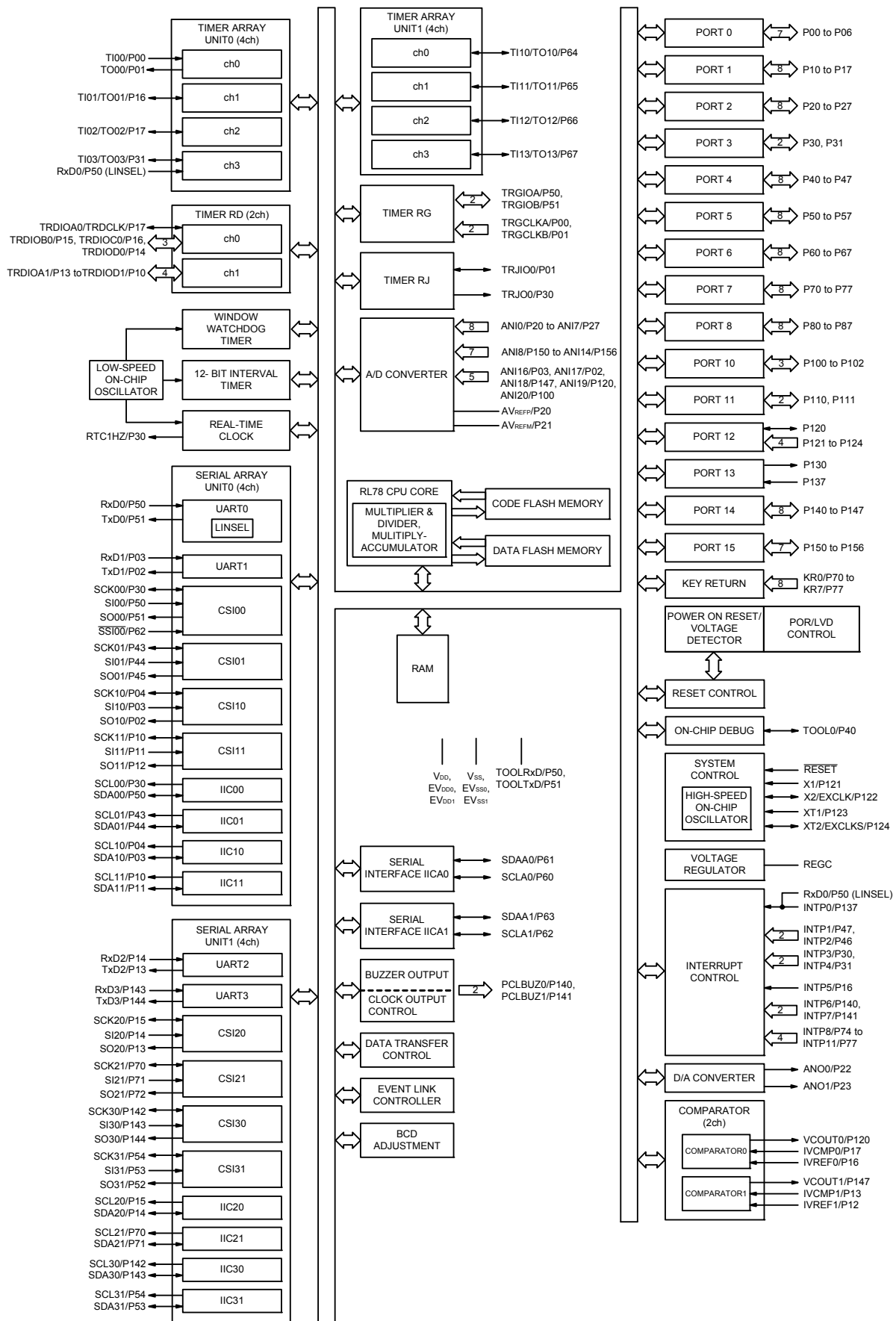


Note Mounted on the 96 KB or more code flash memory products.

1.5.9 80-pin products



1.5.10 100-pin products



(2/2)

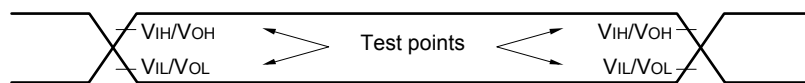
Item		30-pin	32-pin	36-pin	40-pin
		R5F104Ax (x = A, C to E)	R5F104Bx (x = A, C to E)	R5F104Cx (x = A, C to E)	R5F104Ex (x = A, C to E)
Clock output/buzzer output		2	2	2	2
		[30-pin, 32-pin, 36-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: $f_{MAIN} = 20$ MHz operation) [40-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: $f_{MAIN} = 20$ MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: $f_{SUB} = 32.768$ kHz operation)			
8/10-bit resolution A/D converter		8 channels	8 channels	8 channels	9 channels
Serial interface		[30-pin, 32-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel [36-pin, 40-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels			
	I ² C bus	1 channel	1 channel	1 channel	1 channel
Data transfer controller (DTC)		28 sources			29 sources
Event link controller (ELC)		Event input: 19 Event trigger output: 7			Event input: 20 Event trigger output: 7
Vectored interrupt sources	Internal	24	24	24	24
	External	6	6	6	7
Key interrupt		—	—	—	4
Reset		• Reset by RESET pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution ^{Note} • Internal reset by RAM parity error • Internal reset by illegal-memory access			
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V ($T_A = -40$ to +85°C) 1.51 ±0.06 V ($T_A = -40$ to +105°C) • Power-down-reset: 1.50 ±0.04 V ($T_A = -40$ to +85°C) 1.50 ±0.06 V ($T_A = -40$ to +105°C)			
Voltage detector		1.63 V to 4.06 V (14 stages)			
On-chip debug function		Provided			
Power supply voltage		$V_{DD} = 1.6$ to 5.5 V ($T_A = -40$ to +85°C) $V_{DD} = 2.4$ to 5.5 V ($T_A = -40$ to +105°C)			
Operating ambient temperature		$T_A = -40$ to +85°C (A: Consumer applications, D: Industrial applications), $T_A = -40$ to +105°C (G: Industrial applications)			

Note The illegal instruction is generated when instruction code FFH is executed.
 Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

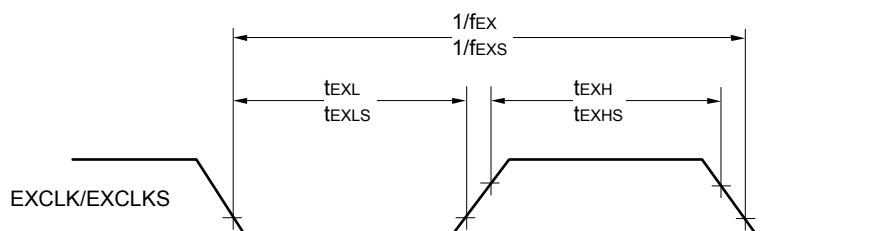
Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xL (x = G, L, M, P): Start address F3F00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

- Remark 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2.** f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3.** f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4.** f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

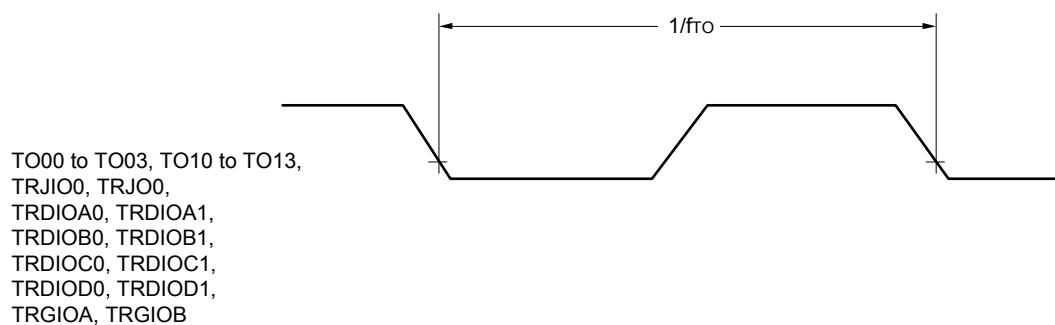
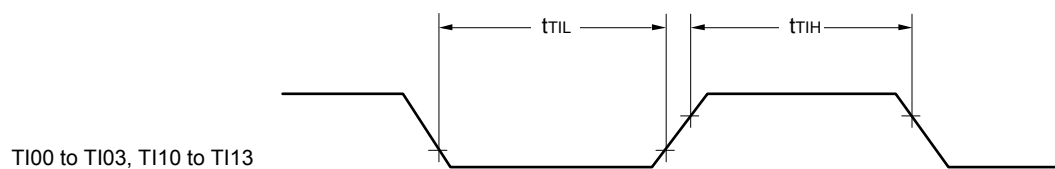
AC Timing Test Points



External System Clock Timing

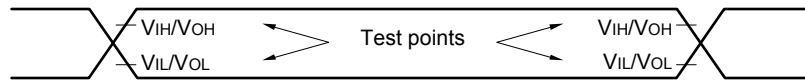


TI/TO Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ EVDD0 ≤ 5.5 V		fMCK/6 Note 2		fMCK/6		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		1.8 V ≤ EVDD0 ≤ 5.5 V		fMCK/6 Note 2		fMCK/6		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		1.7 V ≤ EVDD0 ≤ 5.5 V		fMCK/6 Note 2		fMCK/6 Note 2		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		1.6 V ≤ EVDD0 ≤ 5.5 V	—			fMCK/6 Note 2		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3	—			1.3		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

2.4 V ≤ EVDD0 < 2.7 V: MAX. 2.6 Mbps

1.8 V ≤ EVDD0 < 2.4 V: MAX. 1.3 Mbps

1.6 V ≤ EVDD0 < 1.8 V: MAX. 0.6 Mbps

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fCLK) are:

HS (high-speed main) mode: 32 MHz (2.7 V ≤ VDD ≤ 5.5 V)

16 MHz (2.4 V ≤ VDD ≤ 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V ≤ VDD ≤ 5.5 V)

LV (low-voltage main) mode: 4 MHz (1.6 V ≤ VDD ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with $EV_{DD0} \geq V_b$.

Note 6. The smaller maximum transfer rate derived by using $f_{mck}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $1.8\text{ V} \leq EV_{DD0} < 3.3\text{ V}$ and $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 7. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)**(TA = -40 to +85°C, 1.8 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

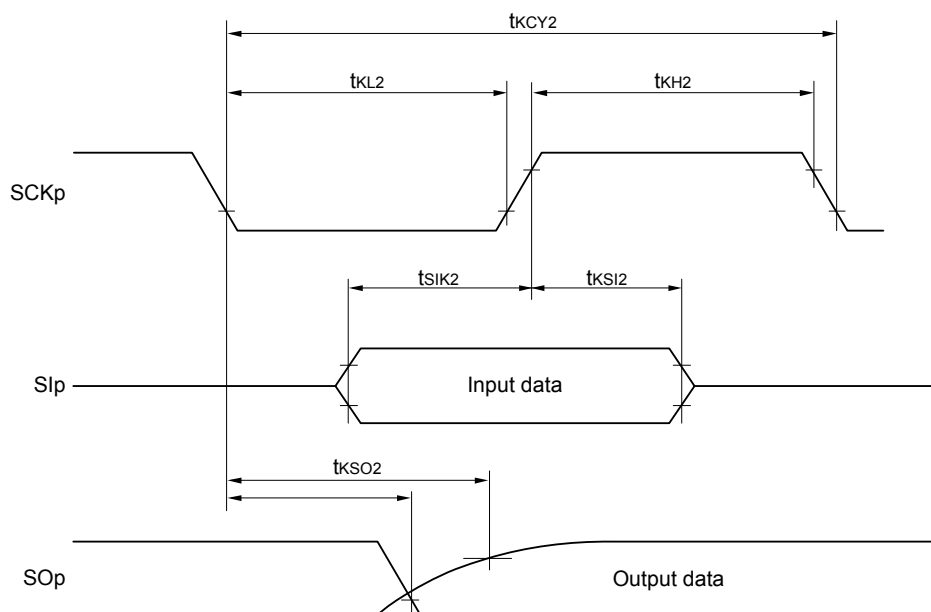
Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK} 4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	300		1150		1150		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	500		1150		1150		ns
		1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V <i>Note</i> , C _b = 30 pF, R _b = 5.5 kΩ	1150		1150		1150		ns
SCKp high-level width	t _{KH1}	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 - 75		t _{KCY1} /2 - 75		t _{KCY1} /2 - 75		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 - 170		t _{KCY1} /2 - 170		t _{KCY1} /2 - 170		ns
		1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V <i>Note</i> , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 - 458		t _{KCY1} /2 - 458		t _{KCY1} /2 - 458		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 - 12		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 - 18		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V <i>Note</i> , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns

Note Use it with EVDD0 ≥ V_b.

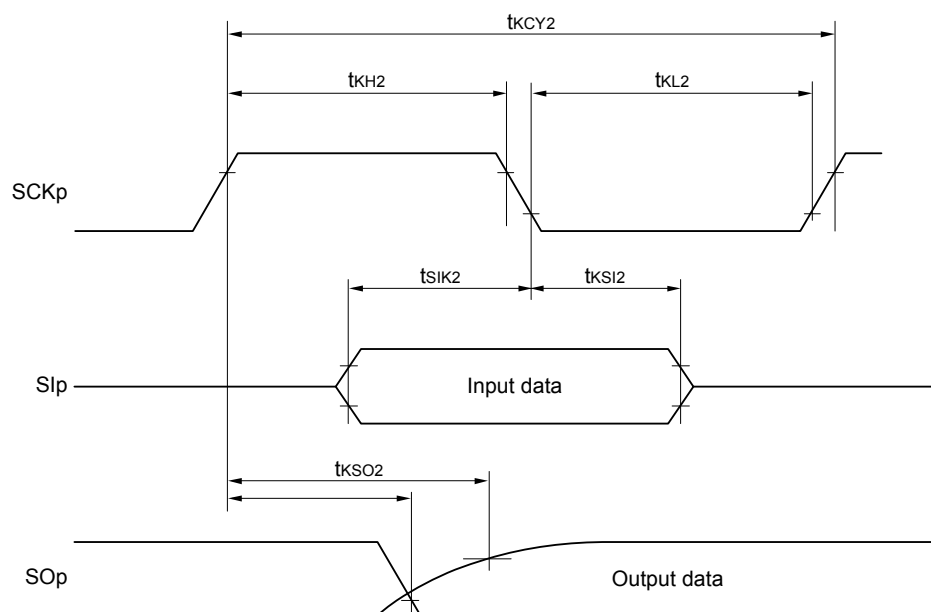
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

2.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fSCL	Standard mode: fCLK ≥ 1 MHz	2.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.8 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EVDD0 ≤ 5.5 V	—		0	100	0	100	kHz
Setup time of restart condition	tSU: STA	2.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		4.7		4.7		μs
Hold time ^{Note 1}	tHD: STA	2.7 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		4.0		4.0		μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		4.7		4.7		μs
Hold time when SCLA0 = "H"	tHIGH	2.7 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		4.0		4.0		μs

(Notes, Caution, and Remark are listed on the next page.)

2.6.2 Temperature sensor characteristics/internal reference voltage characteristic

(TA = -40 to +85°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tAMP		5			μs

2.6.3 D/A converter characteristics

(TA = -40 to +85°C, 1.6 V ≤ EVSS0 = EVSS1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	1.8 V ≤ VDD ≤ 5.5 V			±2.5	LSB
		Rload = 8 MΩ	1.8 V ≤ VDD ≤ 5.5 V			±2.5	LSB
Settling time	tSET	Cload = 20 pF	2.7 V ≤ VDD ≤ 5.5 V			3	μs
			1.6 V ≤ VDD < 2.7 V			6	μs

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = 0\text{ V}$)(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	IDD2 Note 2	HALT mode	HS (high-speed main) mode Note 7	fHOCO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.80	4.36	mA	
					VDD = 3.0 V		0.80	4.36		
				fHOCO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.49	3.67		
					VDD = 3.0 V		0.49	3.67		
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.62	3.42		
					VDD = 3.0 V		0.62	3.42		
				fHOCO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.4	2.85		
					VDD = 3.0 V		0.4	2.85		
			fHOCO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.37	2.08			
				VDD = 3.0 V		0.37	2.08			
			HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.28	2.45	mA	
					Resonator connection		0.40	2.57		
				fMX = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.28	2.45		
					Resonator connection		0.40	2.57		
				fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.19	1.28		
					Resonator connection		0.25	1.36		
		fMX = 10 MHz Note 3, VDD = 3.0 V		Square wave input		0.19	1.28			
				Resonator connection		0.25	1.36			
		Subsystem clock operation	fSUB = 32.768 kHz Note 5, TA = -40°C	Square wave input		0.25	0.57	μA		
				Resonator connection		0.44	0.76			
			fSUB = 32.768 kHz Note 5, TA = +25°C	Square wave input		0.30	0.57			
				Resonator connection		0.49	0.76			
			fSUB = 32.768 kHz Note 5, TA = +50°C	Square wave input		0.36	1.17			
				Resonator connection		0.59	1.36			
			fSUB = 32.768 kHz Note 5, TA = +70°C	Square wave input		0.49	1.97			
				Resonator connection		0.72	2.16			
			fSUB = 32.768 kHz Note 5, TA = +85°C	Square wave input		0.97	3.37			
				Resonator connection		1.16	3.56			
			fSUB = 32.768 kHz Note 5, TA = +105°C	Square wave input		3.20	17.10			
				Resonator connection		3.40	17.50			
	IDD3 Note 6	STOP mode Note 8	TA = -40°C					0.18	0.51	μA
			TA = +25°C					0.24	0.51	
			TA = +50°C					0.29	1.10	
			TA = +70°C					0.41	1.90	
			TA = +85°C					0.90	3.30	
			TA = +105°C					3.10	17.00	

(Notes and Remarks are listed on the next page.)

- (3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		1.2	± 7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI20	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
		10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI20		0		EV_{DD0}	V
		Internal reference voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} Note 3			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} Note 3			V

Note 1. Excludes quantization error ($\pm 1/2$ LSB).

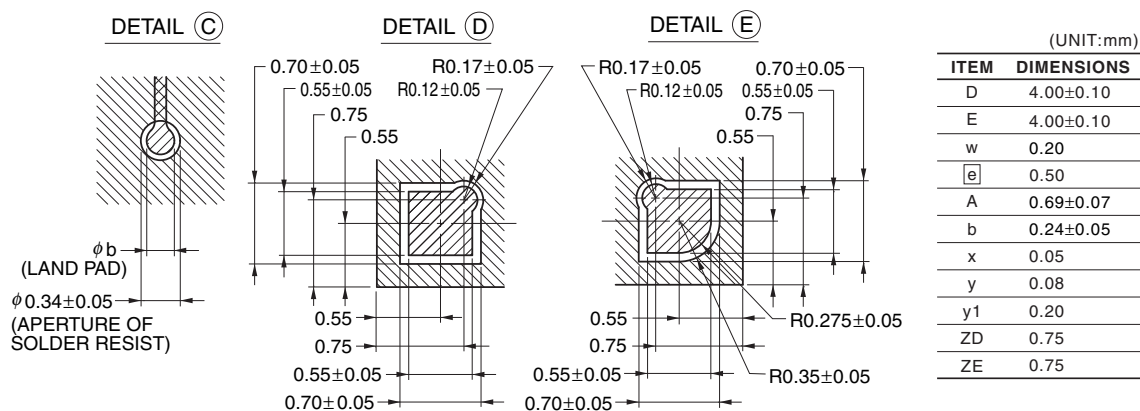
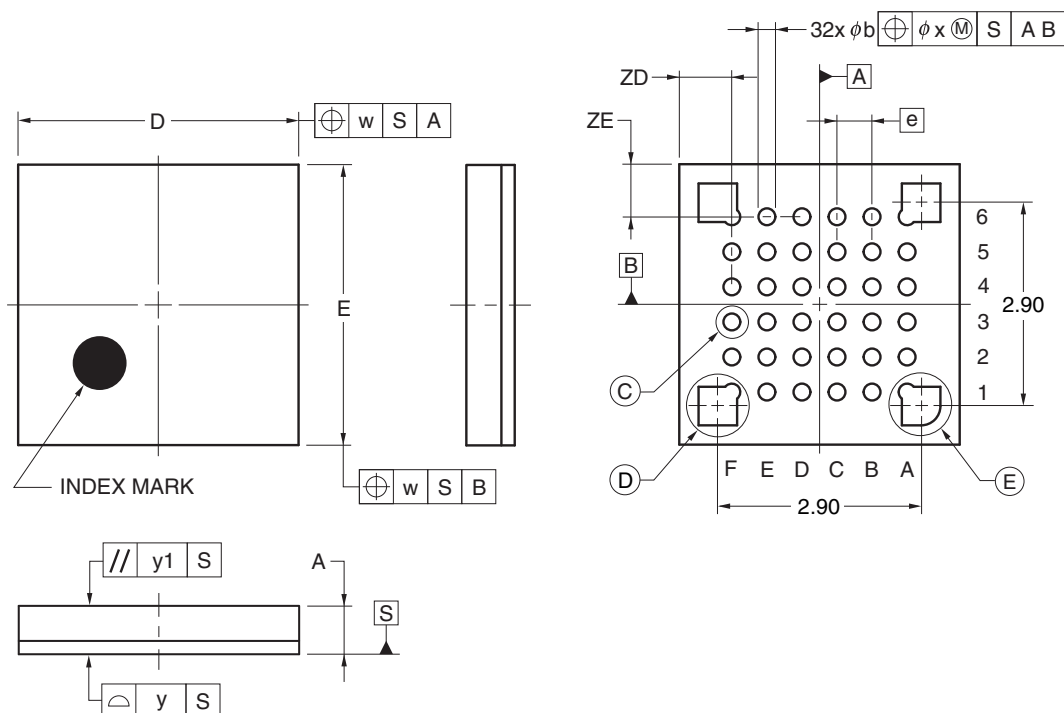
Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

4.3 36-pin products

R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA
R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA

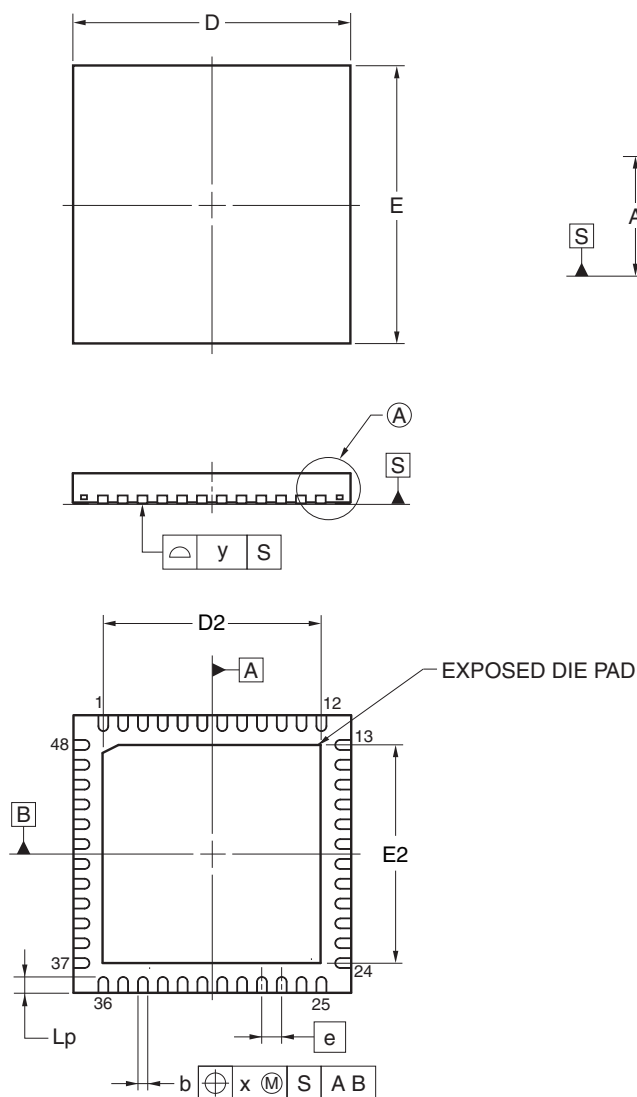
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023



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R5F104GAANA, R5F104GCANA, R5F104GDANA, R5F104GEANA, R5F104GFANA, R5F104GGANA,
 R5F104GHANA, R5F104GJANA
 R5F104GADNA, R5F104GCDNA, R5F104GDDNA, R5F104GEDNA, R5F104GFDNA, R5F104GGDNA,
 R5F104GHDNA, R5F104GJDNA
 R5F104GAGNA, R5F104GCGNA, R5F104GDGNA, R5F104GEGNA, R5F104GFGNA, R5F104GGGNA,
 R5F104GHGNA, R5F104GJGNA
 R5F104GKANA, R5F104GLANA
 R5F104GKGNA, R5F104GLGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-5	0.13

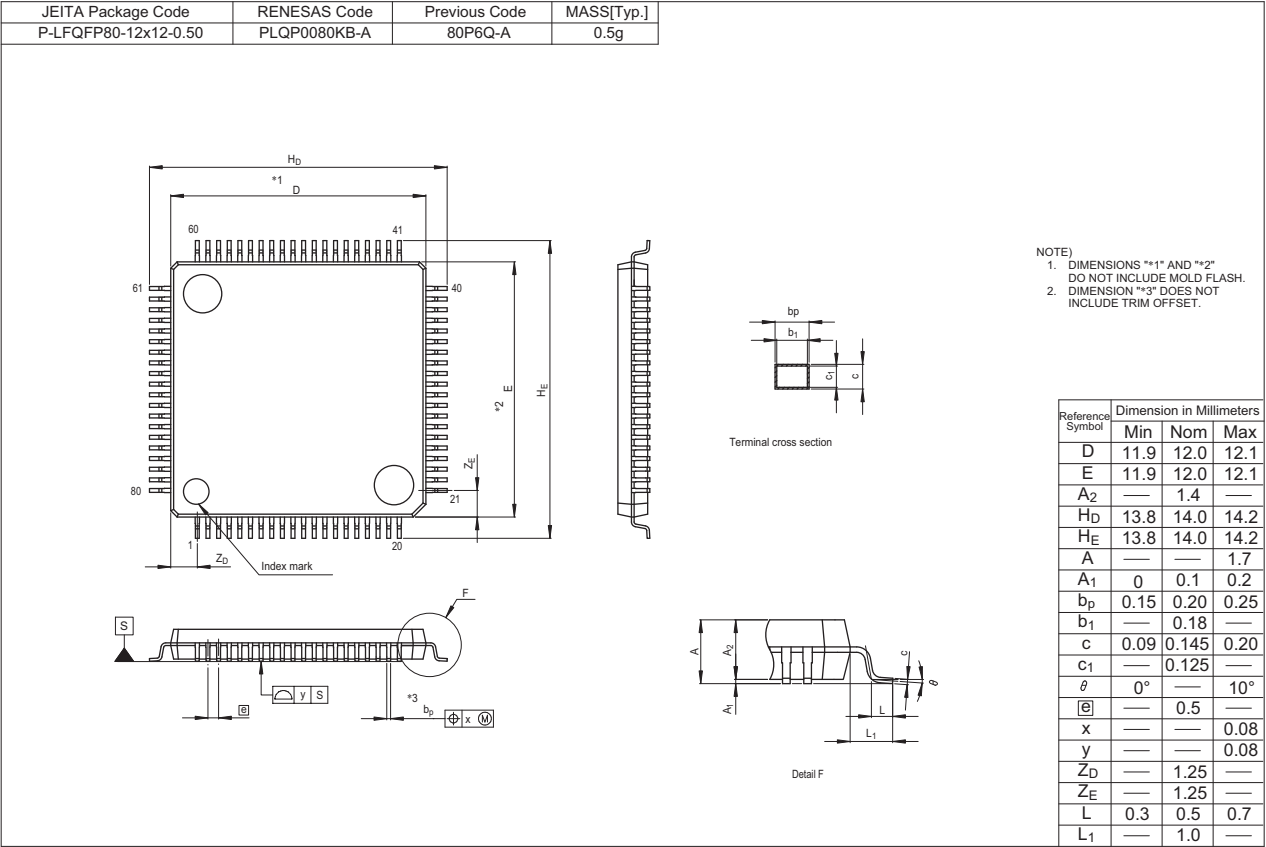


Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.95	7.00	7.05
E	6.95	7.00	7.05
A	0.70	0.75	0.80
b	0.18	0.25	0.30
e	—	0.50	—
Lp	0.30	0.40	0.50
x	—	—	0.05
y	—	—	0.05

ITEM		D2			E2		
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	A	5.45	5.50	5.55	5.45	5.50	5.55

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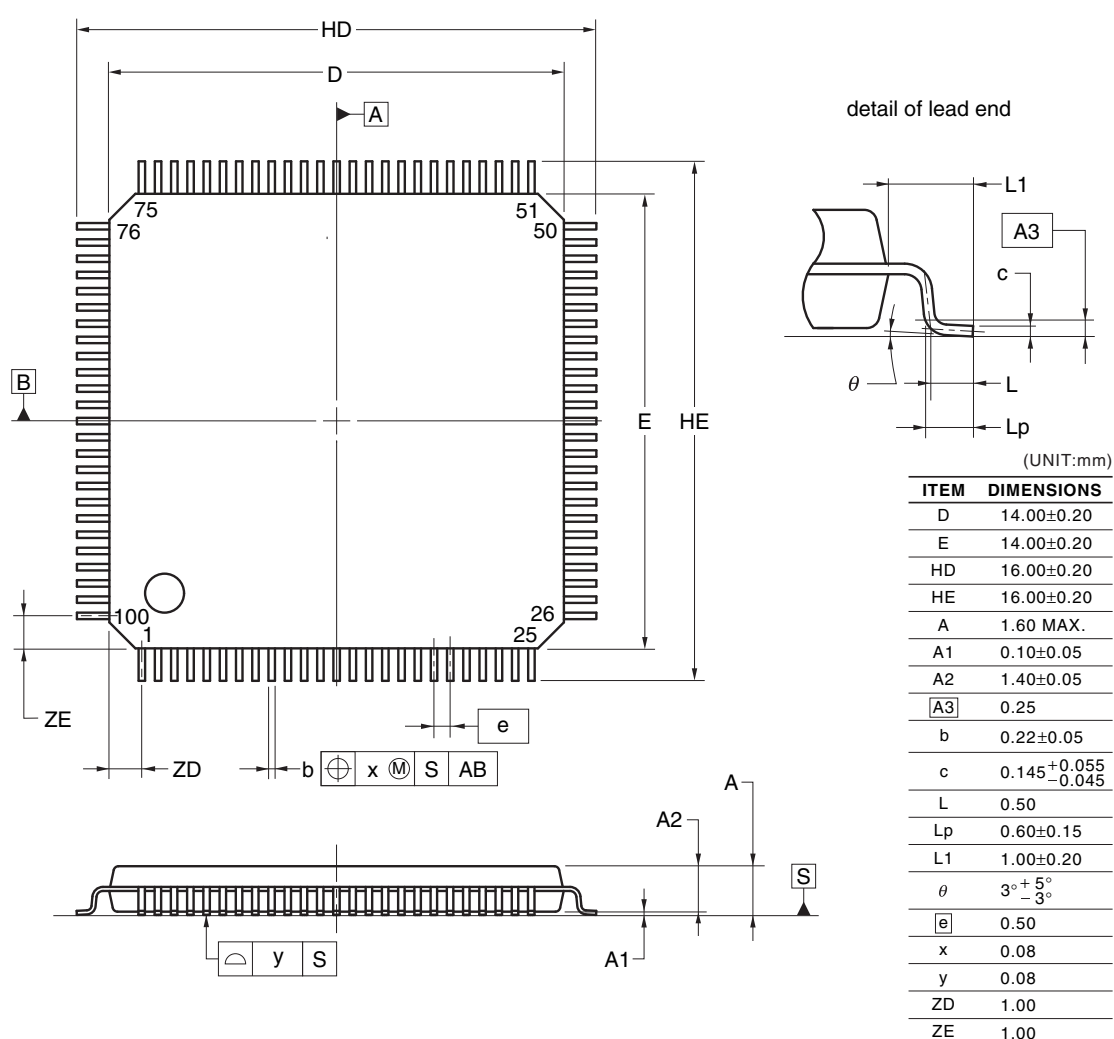
R5F104MKAFB, R5F104MLAFB
R5F104MKGFB, R5F104MLGFB



4.10 100-pin products

R5F104PFAFB, R5F104PGAFA, R5F104PHAFA, R5F104PJAFB
 R5F104PFDFB, R5F104PGDFB, R5F104PHDFB, R5F104PJDFB
 R5F104PFGFB, R5F104PGGFB, R5F104PHGFB, R5F104PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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REVISION HISTORY	RL78/G14 Datasheet
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Rev.	Date	Description	
		Page	Summary
2.00	Oct 25, 2013	112 to 169 171 to 187	Addition of CHAPTER 3 ELECTRICAL SPECIFICATIONS Modification of 4.1 30-pin products to 4.10 100-pin products
3.00	Feb 07, 2014	All 1 2 3 6 to 8 15, 16 17 18, 19 20 21, 22 35, 37, 39, 41, 43, 45, 47 42, 43 46, 47 65 to 68 118 137 to 140 180 189, 190 191 193 to 195 198, 199 201, 202	Addition of products with maximum 512 KB flash ROM and 48 KB RAM Modification of 1.1 Features Modification of ROM, RAM capacities and addition of note 3 Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14 Addition of part number Modification of 1.3.6 48-pin products Modification of 1.3.7 52-pin products Modification of 1.3.8 64-pin products Modification of 1.3.9 80-pin products Modification of 1.3.10 100-pin products Modification of operating ambient temperature in 1.6 Outline of Functions Addition of table of 48-pin, 52-pin, 64-pin products (code flash memory 384 KB to 512 KB) Addition of table of 80-pin, 100-pin products (code flash memory 384 KB to 512 KB) Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products Modification of 2.7 Data Memory Retention Characteristics Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products Modification of 3.7 Data Memory Retention Characteristics Addition and modification of 4.6 48-pin products Modification of 4.7 52-pin products Addition and modification of 4.8 64-pin products Addition and modification of 4.9 80-pin products Addition and modification of 4.10 100-pin products
3.20	Jan 05, 2015	p.2 p.6 p.6 to 8 p.17 p.36, 39, 42, 45, 48, 50, 52 p.46, 48 p.47 p.62, 64, 66, 68, 70, 72	Deletion of R5F104JK and R5F104JL from the list of ROM and RAM capacities and modification of note Deletion of ordering part numbers of R5F104JK and R5F104JL from 52-pin plastic LQFP package in 1.2 Ordering Information Deletion of note 2 in 1.2 Ordering Information Deletion of note 2 in 1.3.7 52-pin products Modification of description in 1.6 Outline of Functions Deletion of description of 52-pin in 1.6 Outline of Functions Modification of note of 1.6 Outline of Functions Modification of specifications in 2.3.2 Supply current characteristics